

Enhanced ultrafast power diode Rev. 02 — 7 March 2011

Product data sheet

Product profile 1.

1.1 General description

Enhanced ultrafast power diode in a SOT404 (D2PAK) surface-mountable plastic package.

1.2 Features and benefits

- High thermal cycling performance
- Low on-state losses
- Low thermal resistance

1.3 Applications

- Dual Mode (DCM and CCM) PFC
- Soft recovery characteristic
- Surface-mountable package
- Power Factor Correction (PFC) for Interleaved Topology

1.4 Quick reference data

Quick reference data Table 1.

Quick reference dat					
Parameter	Conditions	Min	Тур	Max	Unit
repetitive peak reverse voltage		-	-	600	V
average forward current	square-wave pulse; δ = 0.5 ; T _{mb} ≤ 115 °C; see <u>Figure 1;</u> see <u>Figure 2</u>	-	-	9	A
aracteristics					
forward voltage	I _F = 8 A; T _j = 25 °C; see <u>Figure 5</u>	-	1.45	1.9	V
	I _F = 8 A; T _j = 150 °C; see <u>Figure 5</u>	-	1.25	1.7	V
characteristics					
reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/µs; T _j = 25 °C; see <u>Figure 6</u>	-	17.5	35	ns
	repetitive peak reverse voltage average forward current macteristics forward voltage characteristics reverse recovery	$\label{eq:second} \begin{array}{l} \mbox{repetitive peak} \\ \mbox{reverse voltage} \\ \mbox{average forward} \\ \mbox{current} & \mbox{square-wave pulse; } \delta = 0.5 \ ; \\ T_{mb} \leq 115 \ ^{\circ}\mbox{C; see } \underline{Figure 1}; \\ \mbox{see } \underline{Figure 2} \\ \mbox{aracteristics} \\ \mbox{forward voltage} & \mbox{I}_{F} = 8 \ A; \ T_{j} = 25 \ ^{\circ}\mbox{C; see } \underline{Figure 5} \\ \mbox{I}_{F} = 8 \ A; \ T_{j} = 150 \ ^{\circ}\mbox{C; see } \underline{Figure 5} \\ \mbox{characteristics} \\ \mbox{reverse recovery} \\ \mbox{time} & \mbox{I}_{F} = 1 \ A; \ V_{R} = 30 \ V; \\ \mbox{d}_{I_{F}}/dt = 100 \ A/\mus; \ T_{j} = 25 \ ^{\circ}\mbox{C;} \end{array}$	$\label{eq:second} \begin{array}{c} \mbox{repetitive peak} & \mbox{reverse voltage} & \mbox{-}\\ \mbox{average forward} & \mbox{square-wave pulse; } \delta = 0.5 \ ; & \mbox{-}\\ \mbox{T}_{mb} \leq 115 \ ^{\circ}\text{C}; \mbox{see Figure 1}; & \mbox{see Figure 2} \\ \mbox{aracteristics} & \\ \mbox{forward voltage} & \mbox{I}_{F} = 8 \ A; \ T_{j} = 25 \ ^{\circ}\text{C}; \ \mbox{see Figure 5} & \mbox{-}\\ \mbox{I}_{F} = 8 \ A; \ T_{j} = 150 \ ^{\circ}\text{C}; & \mbox{-}\\ \mbox{see Figure 5} & \mbox{-}\\ \mbox{characteristics} & \\ \mbox{reverse recovery} & \mbox{I}_{F} = 1 \ A; \ V_{R} = 30 \ V; & \mbox{-}\\ \mbox{dl}_{F}/dt = 100 \ A/\mus; \ T_{j} = 25 \ ^{\circ}\text{C}; \end{array}$	$\begin{tabular}{ c c c c } \hline repetitive peak & - & - & - \\ \hline repetitive peak \\ reverse voltage & & - & - \\ \hline average forward \\ current & $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $	$\begin{tabular}{ c c c c } \hline repetitive peak \\ reverse voltage & - & - & 600 \\ \hline average forward \\ current & $square-wave pulse; \delta = 0.5 ; & - & - & 9 \\ \hline T_{mb} \leq 115 \ ^\circ C; see \ Figure 1; \\ see \ Figure 2 & & & & & & \\ \hline aracteristics & & & & & & & \\ \hline forward voltage & $I_F = 8 \ A; \ T_j = 25 \ ^\circ C; see \ Figure 5 & - & 1.45 \ 1.9 \\ \hline I_F = 8 \ A; \ T_j = 150 \ ^\circ C; & - & 1.25 \ 1.7 \\ see \ Figure 5 & & & & & & \\ \hline characteristics & & & & & & \\ \hline characteristics & & & & & & & \\ \hline reverse recovery \\ time & $I_F = 1 \ A; \ V_R = 30 \ V; \\ dI_F/dt = 100 \ A/\mus; \ T_j = 25 \ ^\circ C; & & & & & & & & & \\ \hline \end{tabular}$



2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	no connection		
2	К	cathode ^[1]	mb	K — A 001aaa020
3	А	anode		
mb	К	mounting base; cathode		
			SOT404 (D2PAK)	

[1] It is not possible to connect to pin 2 of the SOT404 package.

3. Ordering information

Table 3. Orde	ring information		
Type number	Package		
	Name	Description	Version
BYV29FB-600	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

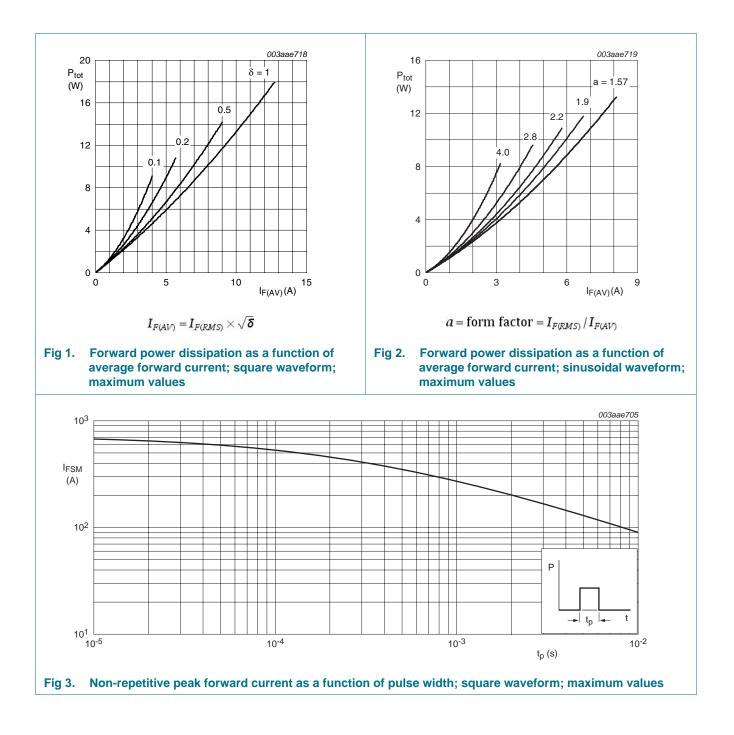
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	square-wave pulse; $\delta = 0.5$; T _{mb} \leq 115 °C; see Figure 1; see Figure 2	-	9	А
I _{FRM}	repetitive peak forward current	square-wave pulse; δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 115 °C	-	18	А
I _{FSM}	non-repetitive peak forward current	$t_p = 10 \text{ ms}$; sine-wave pulse; $T_{j(init)} = 25 \text{ °C}$; see <u>Figure 3</u>	-	91	А
		t _p = 8.3 ms; sine-wave pulse; T _{j(init)} = 25 °C; see <u>Figure 3</u>	-	100	А
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

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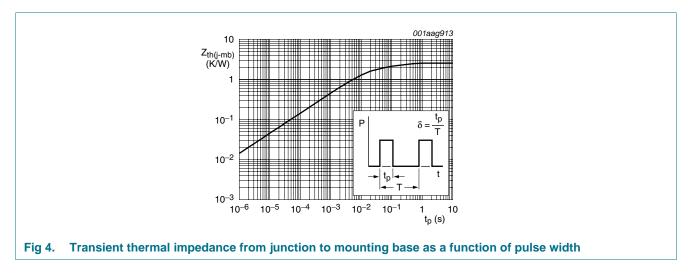


5. Thermal characteristics

Table 5.	Thermal	characteristics
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 4	-	-	2.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	50	-	K/W

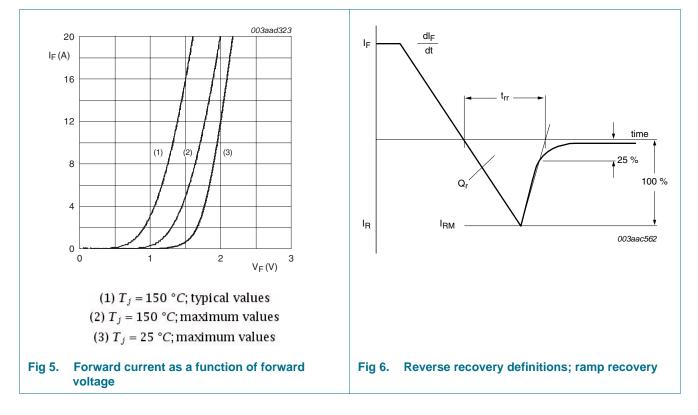
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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6. Characteristics

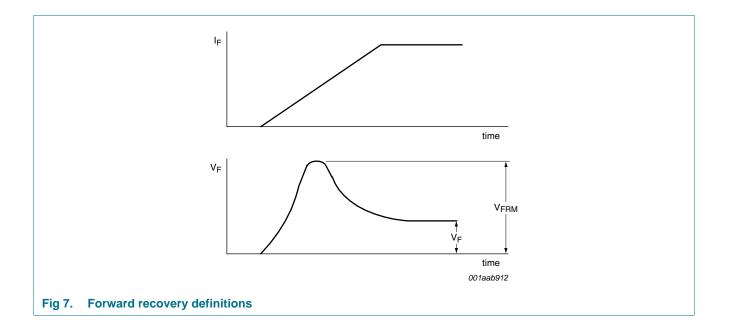
Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; see <u>Figure 5</u>	-	1.45	1.9	V
		I _F = 8 A; T _j = 150 °C; see <u>Figure 5</u>	-	1.25	1.7	V
I _R	reverse current	V _R = 600 V; T _j = 100 °C	-	-	1.5	mA
		V _R = 600 V; T _j = 25 °C	-	-	50	μΑ
Dynamic	characteristics					
Q _r	recovered charge	I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/μs; see <u>Figure 6</u>	-	13	-	nC
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/μs; T _j = 25 °C; see <u>Figure 6</u>	-	17.5	35	ns
I _{RM}	peak reverse recovery current	I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/μs; see <u>Figure 6</u>	-	1.5	-	А
V _{FR}	forward recovery voltage	I _F = 1 A; dI _F /dt = 100 A/μs; see Figure 7	-	3.2	-	V



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7. Package outline

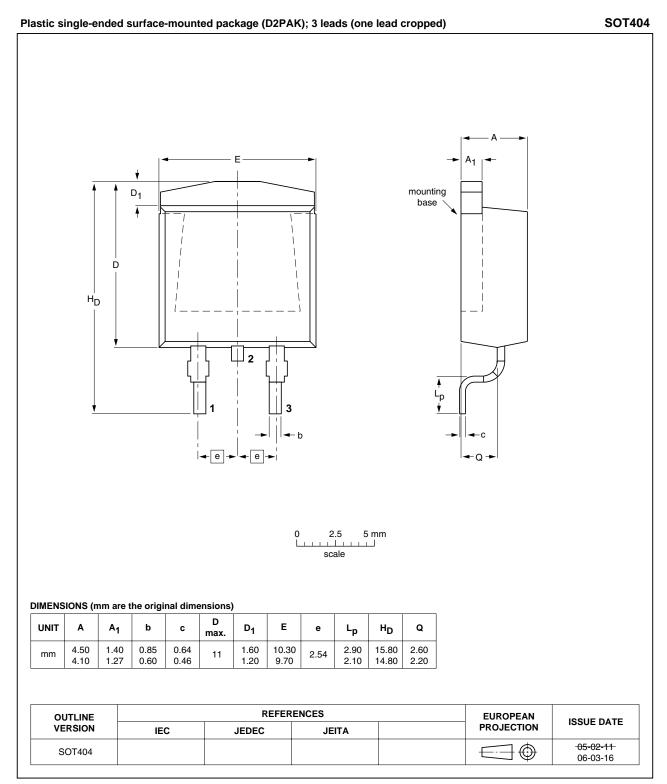


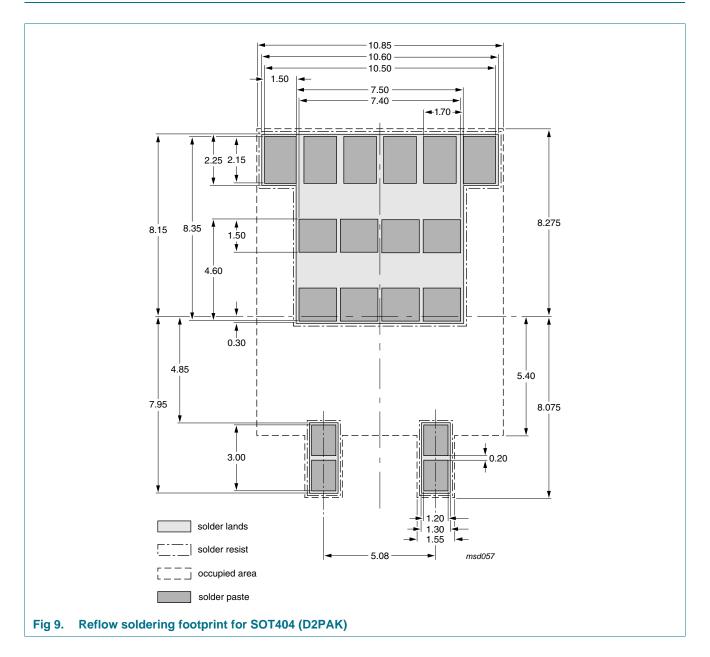
Fig 8. Package outline SOT404 (D2PAK)

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8. Soldering





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9. Revision history

Table 7.Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV29FB-600 v.2	20110307	Product data sheet	-	BYV29FB-600 v.1
Modifications:	 Various chang 	es to content.		
BYV29FB-600 v.1	20100907	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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